

**Amendments to the Specification:**

Please replace the paragraph beginning at page 6, line 2, with the following rewritten paragraph (with deletions shown in strike-out and additions shown in underlining):

FIG. 1B illustrates the cross-sectional view of the semiconductor device in which an ion is implanted into the semiconductor substrate 1, where an N well (~~not shown~~1a) will be formed, using a given mask. FIG. 1C illustrates the cross-sectional view of the semiconductor device in which an ion is implanted into the semiconductor substrate 1, where a P well (~~not shown~~1b) will be formed, using a given mask. At this time, the sacrificial oxide film 2 is used as a screen oxide film for prohibiting internal diffusion due to dopant channeling..

Please replace the paragraph beginning at page 9, line 10, with the following rewritten paragraph (with deletions shown in strike-out and additions shown in underlining)

FIG. 3B illustrates the cross-sectional view of the semiconductor device in which an ion is implanted into the semiconductor substrate 11, where an N well (~~not shown~~11a) will be formed, using a given mask. FIG. 3C illustrates the cross-sectional view of the semiconductor device in which an ion is implanted into the semiconductor substrate 11, where a P well (~~not shown~~11b) will be formed, using a given mask. At this time, the sacrificial oxide film 12 is used as a screen oxide film for prohibiting internal diffusion due to dopant channeling.